

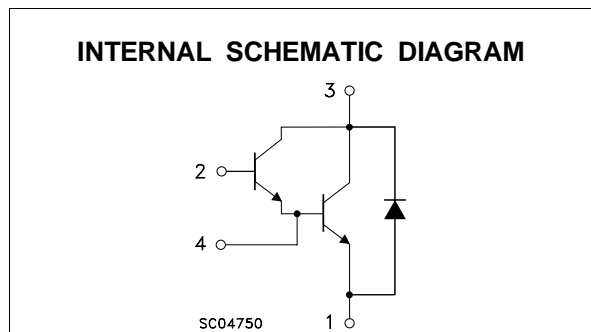
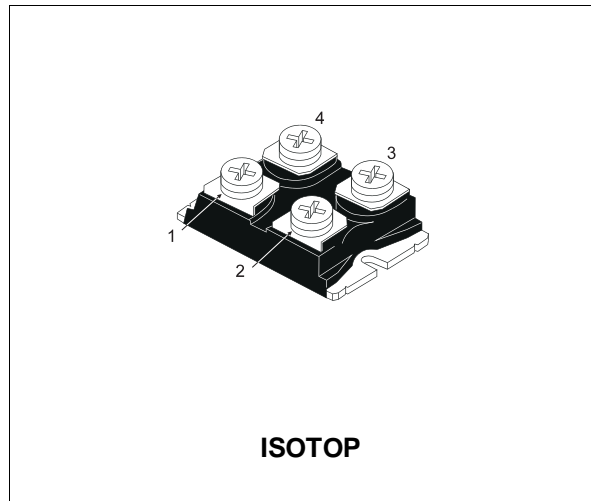


## NPN DARLINGTON POWER MODULE

- HIGH CURRENT POWER BIPOLAR MODULE
- VERY LOW  $R_{th}$  JUNCTION CASE
- SPECIFIED ACCIDENTAL OVERLOAD AREAS
- ULTRAFAST FREEWHEELING DIODE
- FULLY INSULATED PACKAGE (UL COMPLIANT)
- EASY TO MOUNT
- LOW INTERNAL PARASITIC INDUCTANCE

### INDUSTRIAL APPLICATIONS:

- MOTOR CONTROL
- SMPS & UPS
- WELDING EQUIPMENT



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CEV}$	Collector-Emitter Voltage ( $V_{BE} = -5$ V)	600	V
$V_{CEO(sus)}$	Collector-Emitter Voltage ( $I_B = 0$ )	450	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	7	V
$I_C$	Collector Current	60	A
$I_{CM}$	Collector Peak Current ( $t_p = 10$ ms)	90	A
$I_B$	Base Current	6	A
$I_{BM}$	Base Peak Current ( $t_p = 10$ ms)	12	A
$P_{tot}$	Total Dissipation at $T_c = 25$ °C	175	W
$V_{isol}$	Insulation Withstand Voltage (RMS) from All Four Terminals to External Heatsink	2500	V
$T_{stg}$	Storage Temperature	-55 to 150	°C
$T_j$	Max. Operating Junction Temperature	150	°C

# ESM5045DV

## THERMAL DATA

R <sub>thj-case</sub>	Thermal Resistance Junction-case (transistor)	Max	0.71	°C/W
R <sub>thj-case</sub>	Thermal Resistance Junction-case (diode)	Max	1.2	°C/W
R <sub>thc-h</sub>	Thermal Resistance Case-heatsink With Conductive Grease Applied	Max	0.05	°C/W

## ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I <sub>CER</sub> #	Collector Cut-off Current (R <sub>BE</sub> = 5 Ω)	V <sub>CE</sub> = V <sub>CEV</sub> V <sub>CE</sub> = V <sub>CEV</sub> T <sub>j</sub> = 100 °C			1.5 20	mA mA
I <sub>CEV</sub> #	Collector Cut-off Current (V <sub>BE</sub> = -5)	V <sub>CE</sub> = V <sub>CEV</sub> V <sub>CE</sub> = V <sub>CEV</sub> T <sub>j</sub> = 100 °C			1 13	mA mA
I <sub>EBO</sub> #	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 5 V			1	mA
V <sub>CEO(SUS)</sub> *	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 0.2 A L = 25 mH V <sub>clamp</sub> = 450 V	450			V
h <sub>FE</sub> *	DC Current Gain	I <sub>C</sub> = 50 A V <sub>CE</sub> = 5 V		150		
V <sub>CE(sat)</sub> *	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 35 A I <sub>B</sub> = 0.7 A I <sub>C</sub> = 35 A I <sub>B</sub> = 0.7 A T <sub>j</sub> = 100 °C I <sub>C</sub> = 50 A I <sub>B</sub> = 2.8 A I <sub>C</sub> = 50 A I <sub>B</sub> = 2.8 A T <sub>j</sub> = 100 °C		1.2 1.4 1.4 1.6	2 2	V V V V
V <sub>BE(sat)</sub> *	Base-Emitter Saturation Voltage	I <sub>C</sub> = 50 A I <sub>B</sub> = 2.8 A I <sub>C</sub> = 50 A I <sub>B</sub> = 2.8 A T <sub>j</sub> = 100 °C		2.3 2.3	3	V V
di <sub>C</sub> /dt	Rate of Rise of On-state Collector	V <sub>CC</sub> = 300 V R <sub>C</sub> = 0 t <sub>p</sub> = 3 μs I <sub>B1</sub> = 1.05 A T <sub>j</sub> = 100 °C	300	400		A/μs
V <sub>CE(3 μs)</sub> **	Collector-Emitter Dynamic Voltage	V <sub>CC</sub> = 300 V R <sub>C</sub> = 8.5 Ω I <sub>B1</sub> = 1.05 A T <sub>j</sub> = 100 °C		4.5	8	V
V <sub>CE(5 μs)</sub> **	Collector-Emitter Dynamic Voltage	V <sub>CC</sub> = 300 V R <sub>C</sub> = 8.5 Ω I <sub>B1</sub> = 1.05 A T <sub>j</sub> = 100 °C		2.5	4.5	V
t <sub>s</sub> t <sub>f</sub> t <sub>c</sub>	Storage Time Fall Time Cross-over Time	I <sub>C</sub> = 35 A V <sub>CC</sub> = 50 V V <sub>BB</sub> = -5 V R <sub>BB</sub> = 0.6 Ω V <sub>clamp</sub> = 450 V I <sub>B1</sub> = 0.7 A L = 0.07 mH T <sub>j</sub> = 100 °C		3.2 0.25 0.75	5 0.5 1.5	μs μs μs
V <sub>CEW</sub>	Maximum Collector Emitter Voltage Without Snubber	I <sub>CWoff</sub> = 60 A I <sub>B1</sub> = 2.8 A V <sub>BB</sub> = -5 V V <sub>CC</sub> = 50 V L = 42 μH R <sub>BB</sub> = 0.6 Ω T <sub>j</sub> = 125 °C	450			V
V <sub>F</sub> *	Diode Forward Voltage	I <sub>F</sub> = 50 A T <sub>j</sub> = 100 °C		1.5	1.8	V
I <sub>RM</sub>	Reverse Recovery Current	V <sub>CC</sub> = 200 V I <sub>F</sub> = 50 A di <sub>F</sub> /dt = -300 A/μs L < 0.05 μH T <sub>j</sub> = 100 °C		32	38	A

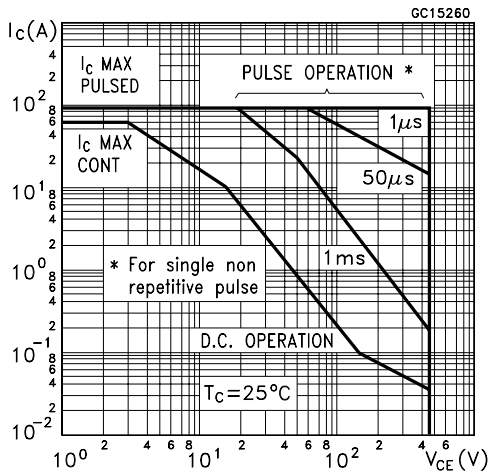
\* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

To evaluate the conduction losses of the diode use the following equations:

$$V_F = 1.5 + 0.0055 I_F \quad P = 1.5 I_{F(AV)} + 0.0055 I_{F(RMS)}^2$$

# See test circuits in databook introduction

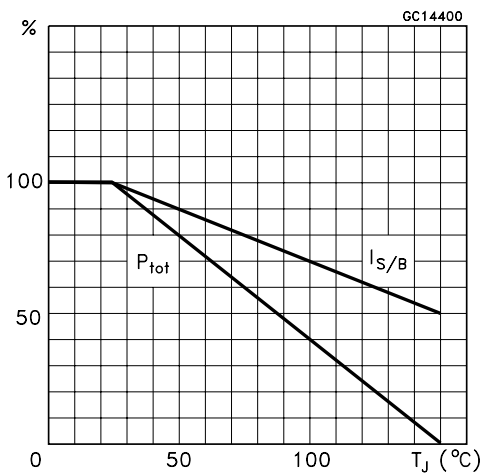
Safe Operating Areas



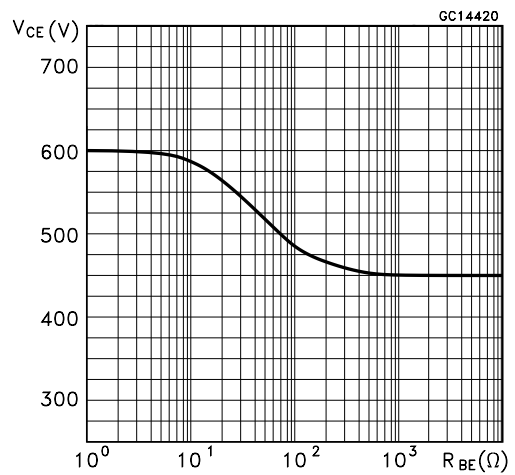
Thermal Impedance



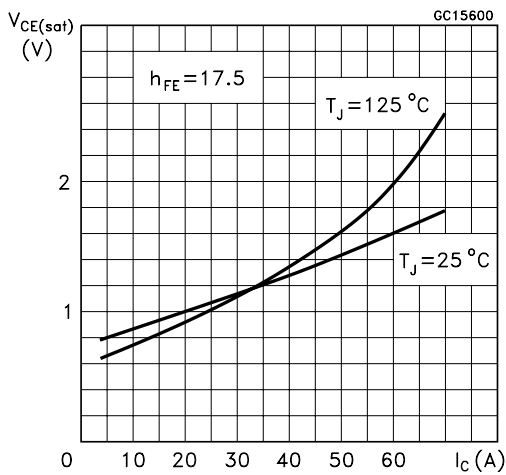
Derating Curve



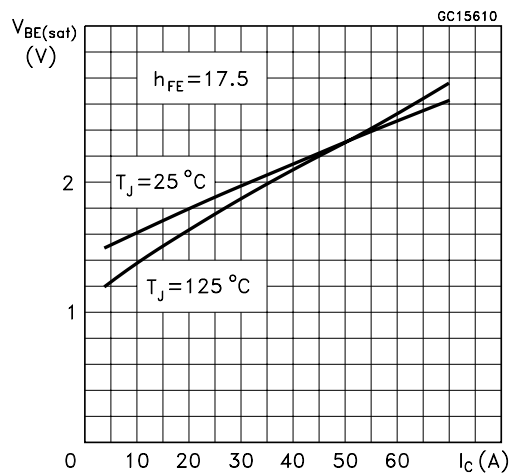
Collector-emitter Voltage Versus base-emitter Resistance



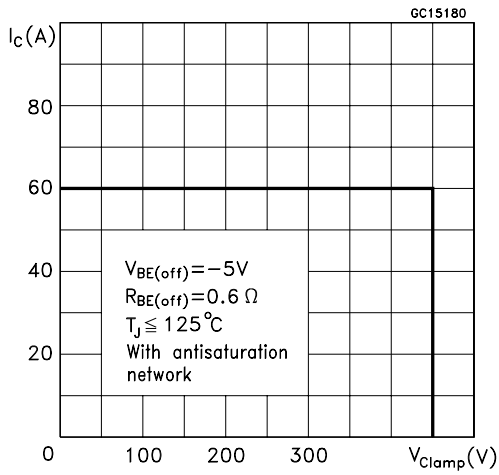
Collector Emitter Saturation Voltage



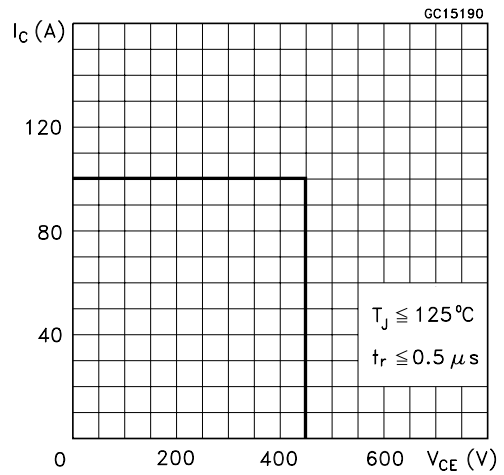
Base-Emitter Saturation Voltage



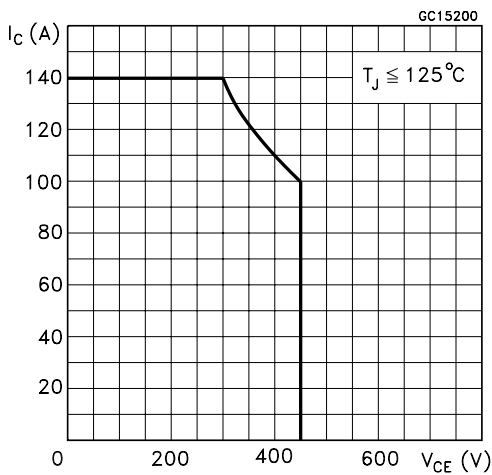
Reverse Biased SOA



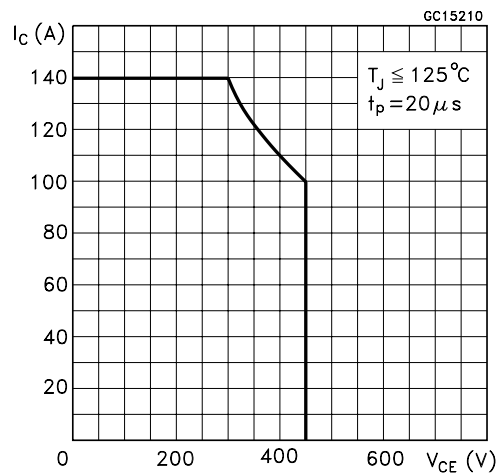
Forward Biased SOA



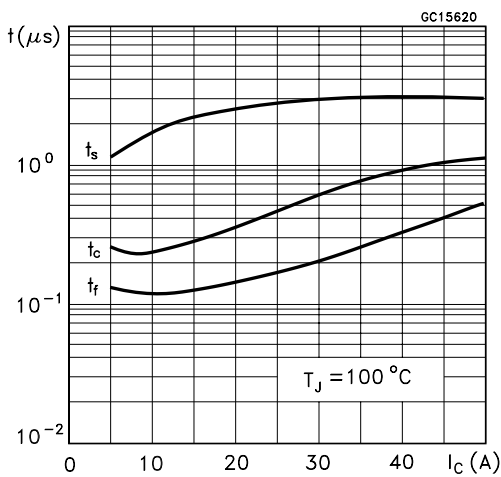
Reverse Biased AOA



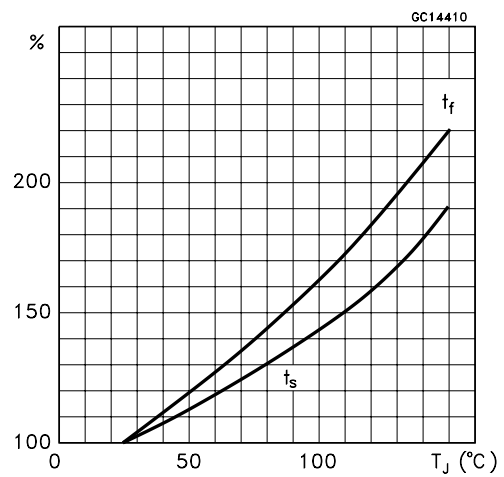
Forward Biased AOA



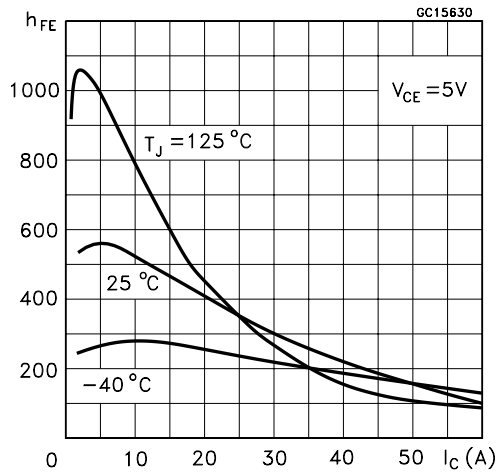
Switching Times Inductive Load



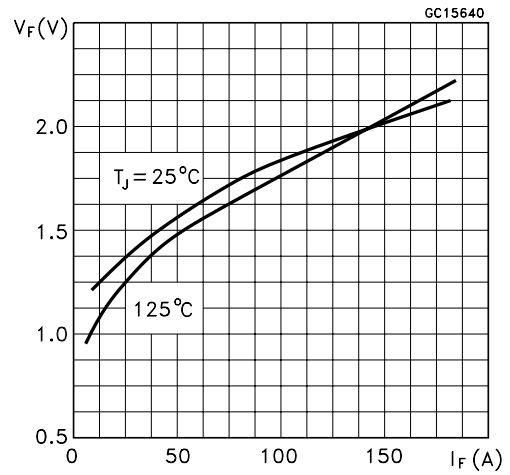
Switching Times Inductive Load Versus Temperature



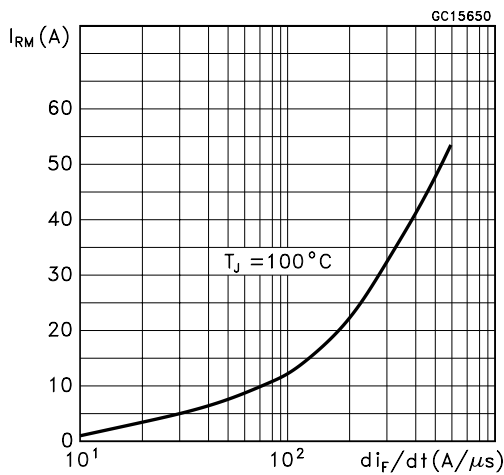
Dc Current Gain



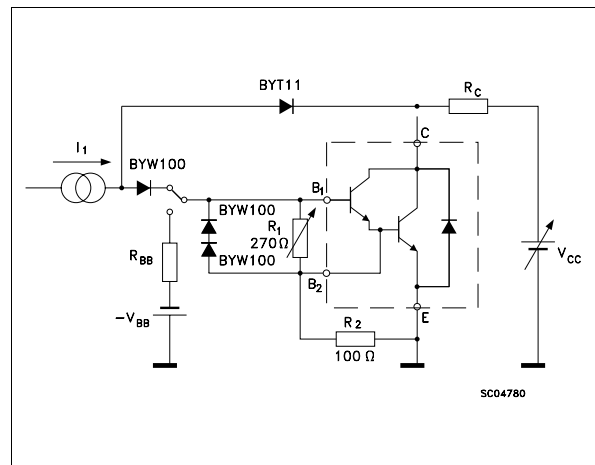
Typical  $V_F$  Versus  $I_F$



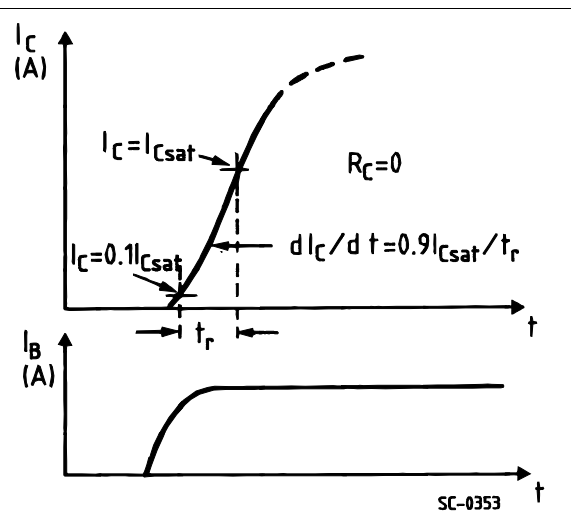
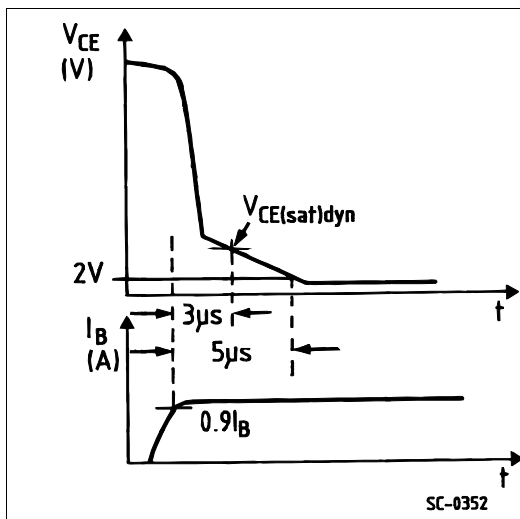
Peak Reverse Current Versus  $di_F/dt$



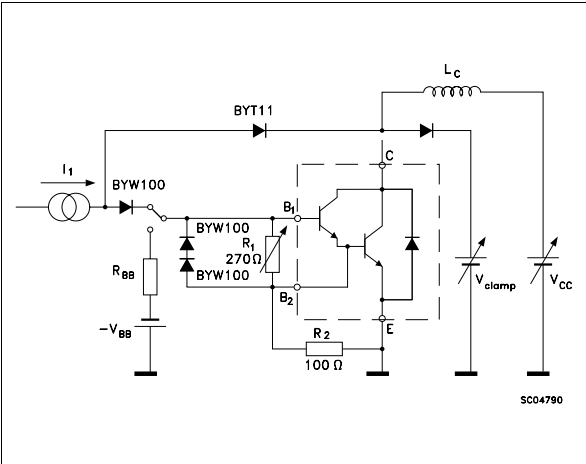
Turn-on Switching Test Circuit



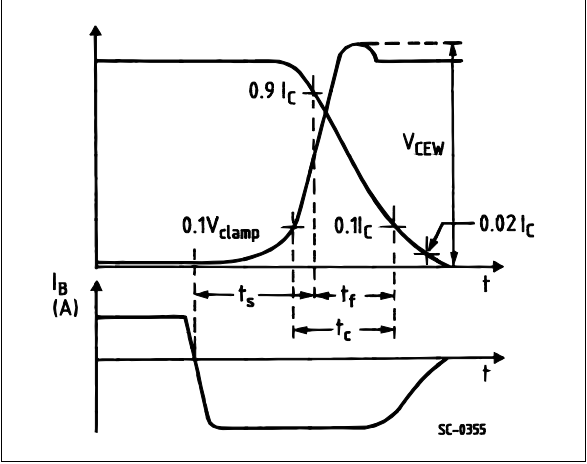
Turn-on Switching Waveforms



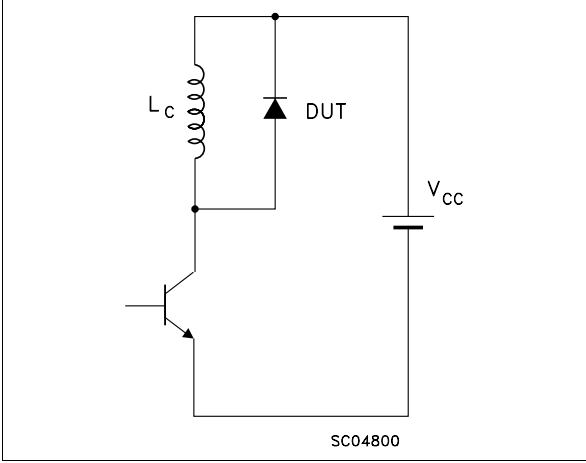
Turn-on Switching Test Circuit



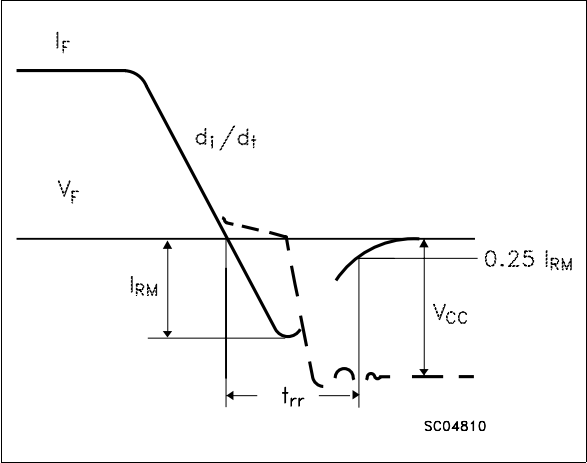
Turn-off Switching Waveforms



Turn-off Switching Test Circuit of Diode

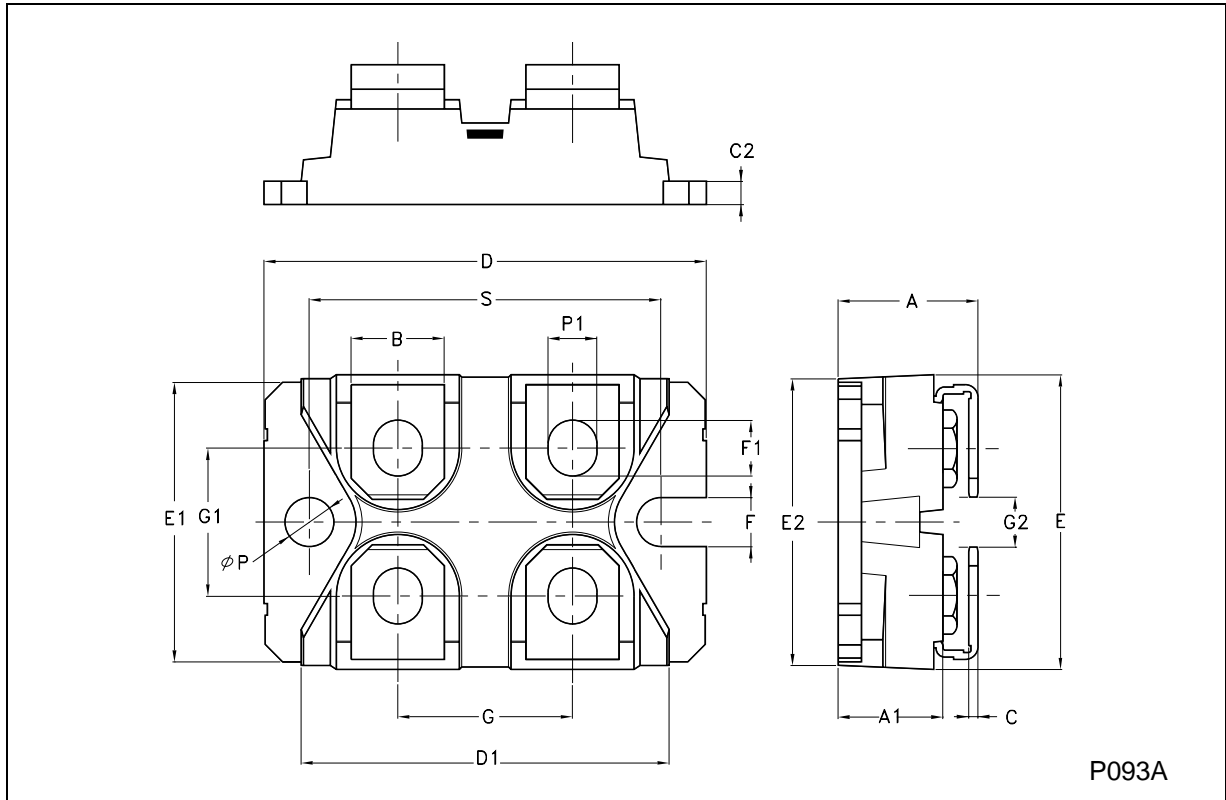


Turn-off Switching Waveform of Diode



**ISOTOP MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.8		12.2	0.465		0.480
A1	8.9		9.1	0.350		0.358
B	7.8		8.2	0.307		0.322
C	0.75		0.85	0.029		0.033
C2	1.95		2.05	0.076		0.080
D	37.8		38.2	1.488		1.503
D1	31.5		31.7	1.240		1.248
E	25.15		25.5	0.990		1.003
E1	23.85		24.15	0.938		0.950
E2		24.8			0.976	
G	14.9		15.1	0.586		0.594
G1	12.6		12.8	0.496		0.503
G2	3.5		4.3	0.137		1.169
F	4.1		4.3	0.161		0.169
F1	4.6		5	0.181		0.196
P	4		4.3	0.157		0.169
P1	4		4.4	0.157		0.173
S	30.1		30.3	1.185		1.193



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